



**Mechanical date:**  $A_x=590\mu\text{m}$ ,  $A_y=450\mu\text{m}$   
 $B=100\mu\text{m}$

**Schematic and pinning diagram**

**Chip thickness:**  $138\pm 12\ \mu\text{m}$

**Scribe Line width** -  $60\mu\text{m}$ .

**Top Metal:** Al - for wire bonding.

**Back side - Anode:** Ti-Ni-Ag for soldering

**Probing:sampling testing:** no bad dice inking, guaranteed good dice quantity  $\geq 93\%$ .

### Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	$V_{RWM}$	-	5,0	V
Peak Pulse Power	$P_{pp}$	$t_p=8/20\mu\text{s}$	40*	W
Peak Pulse Current	$I_{pp}$	$t_p=8/20\mu\text{s}$	3,5*	A
Electrostatic Discharge	$V_{ESD}$	IEC 61000-4-2, level 4.	>8 (Contact); >15 (Air).	kV
Max.junction temperature	$T_j$	-	+150	$^{\circ}\text{C}$

### Characteristics ( $T_j=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{BR}$	Breakdown voltage	$I_R=1\text{mA}$	6,15	6,5	7,15	V
$I_R$	Reverse leakage current	$V=5.0\text{V}$	-	10	35	nA
$V_{CL}$	Clamping Voltage	$I_{pp}=1.0\text{A}$ , $t_p=8/20\mu\text{s}$ $I_{pp}=2.5\text{A}$ , $t_p=8/20\mu\text{s}$ $I_{pp}=3.5\text{A}$ , $t_p=8/20\mu\text{s}$	-	-	9* 11* 12*	V
$C_J$	Diode capacitance	$V_R=0\ \text{V}$ , $f=1\text{MHz}$	-	28	31	pF
$R_{diff}$	Differential resistance	$I_R=1\text{mA}$	-	20	100	Ohm

\*- For Device testing